Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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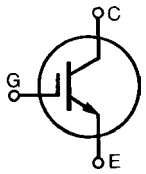
IXYS

IGBT

IXGA 20N100
IXGP 20N100

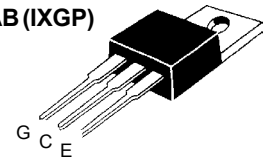
V_{CES} = 1000 V
I_{C25} = 40 A
$V_{CE(sat)}$ = 3.0 V

Preliminary Data Sheet

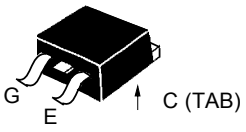


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1000	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	1000	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	40	A
I_{C90}	T_C = 90°C	20	A
I_{CM}	T_C = 25°C, 1 ms	80	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 47 Ω Clamped inductive load, L = 300 μH	I_{CM} = 40 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque with screw M3 Mounting torque with screw M3.5	0.45/4 0.55/5	Nm/lb.in. Nm/lb.in.
Weight	TO-220 TO-263	4 2	g g

TO-220AB (IXGP)



TO-263 AA (IXGA)



Symbol (T_J = 25°C, unless otherwise specified)	Test Conditions		Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 1 mA, V_{GE} = 0 V		1000			V
$V_{GE(th)}$	I_C = 250 μA, V_{CE} = V_{GE}		2.5		5.0	V
I_{CES}	V_{CE} = V_{CES}	T_J = 25°C			250	μA
	V_{GE} = 0 V	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{CE90}, V_{GE} = 15			2.2	3.0	V

Features

- International standard packages JEDEC TO-220AB and TO-263AA
- High current handling capability
- MOS Gate turn-on
  - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies
- Capacitor discharge

Advantages

- Easy to mount with one screw
- Reduces assembly time and cost
- High power density

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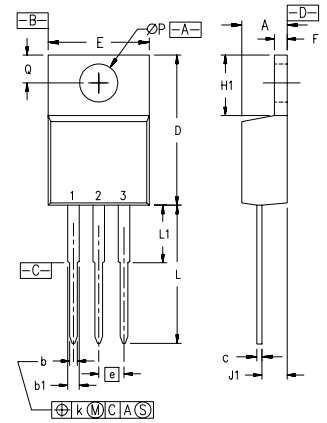
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	12	16		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1750		pF
C_{oes}			100		pF
C_{res}			38		pF
$I_{C(ON)}$	V_{GE} = 10V, V_{CE} = 10V		90		A
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		73		nC
Q_{ge}			13		nC
Q_{gc}			26		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		30		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		30		ns
$t_{d(off)}$	V_{CE} = 800 V, $R_G = R_{off}$ = 47 Ω		350	700	ns
t_{fi}	Remarks: Switching times may		280	700	ns
E_{off}	increase for V_{CE} (Clamp) > 0.8 V_{CES}, higher T_J or increased R_G		3.5	8.0	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		30		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V		30		ns
E_{on}	V_{CE} = 800 V, $R_G = R_{off}$ = 47 Ω		0.65		mJ
$t_{d(off)}$	Remarks: Switching times may		700		ns
t_{fi}	increase for V_{CE} (Clamp) > 0.8 V_{CES},		520		ns
E_{off}	higher T_J or increased R_G		6.5		mJ
R_{thJC}				0.83	K/W
R_{thCK}	TO-220		0.5		K/W

TO-220 AB Dimensions

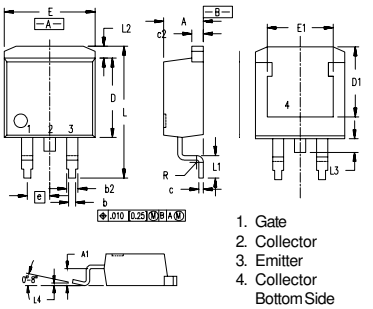


Pins: 1 - Gate 2 - Collector
3 - Emitter 4 - Collector
Bottom Side

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

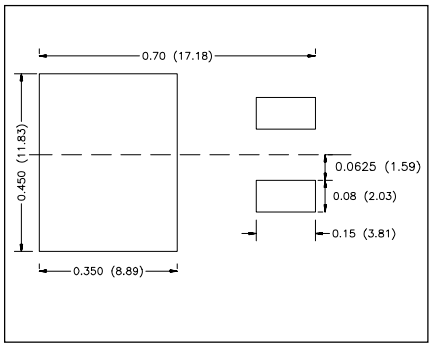
NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-220 AB.

TO-263 AA Outline



1. Gate
2. Collector
3. Emitter
4. Collector
Bottom Side

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029



Min. Recommended Footprint
(Dimensions in inches and mm)

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025